

ABSTRACT

This invention is characterized in that, a gate electrode 27F formed on a P-type well 3 via a gate oxide film 9, a high-concentration N-type source layer and a high-concentration N-type drain layer 15 respectively formed apart from the gate electrode and a low-concentration N-type source layer and a low-concentration N-type drain layer respectively formed so that they respectively surround the N-type source layer and the N-type drain layer 10 and respectively parted by a P-type body layer formed under the gate electrode 27F are provided.